

## NCE N-Channel Enhancement Mode Power MOSFET

### Description

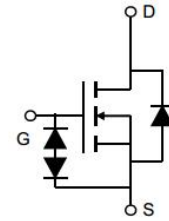
The NCE3404E uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch and PWM applications.

### General Features

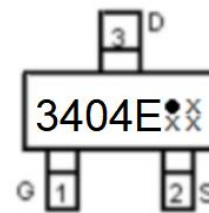
- $V_{DS} = 30V, I_D = 5.8A$   
 $R_{DS(ON)} < 30m\Omega @ V_{GS}=10V$   
 $R_{DS(ON)} < 42m\Omega @ V_{GS}=4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface mount package
- ESD Rating: HBM  $\geq 1500V$

### Application

- Load switch
- PWM application



Schematic diagram



Marking and pin assignment



SOT-23 top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3404E	NCE3404E	SOT-23	Ø180mm	8 mm	3000 units

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	5.8	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	20	A
Maximum Power Dissipation	$P_D$	1.9	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	65.8	$^\circ C/W$
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### Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

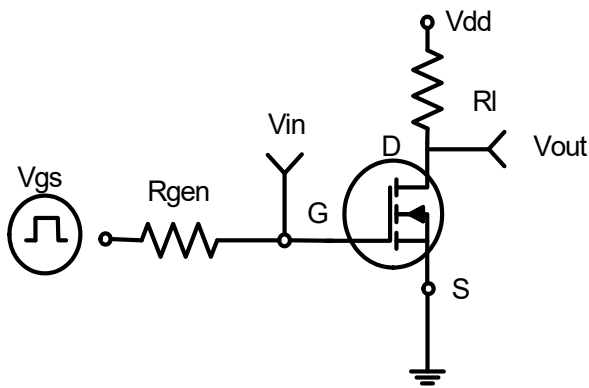
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$	-	-	1	$\mu A$

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±10	uA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.1	1.6	2.2	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =5A	-	21	30	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	-	33	42	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =5A	-	15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, F=1.0MHz	-	639	-	PF
Output Capacitance	C <sub>OSS</sub>		-	60	-	PF
Reverse Transfer Capacitance	C <sub>rSS</sub>		-	51	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, R <sub>L</sub> =3Ω V <sub>GS</sub> =10V, R <sub>GEN</sub> =3Ω	-	5.5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	3.5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	15.5	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4.0	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =5A, V <sub>GS</sub> =10V	-	15.3	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.8	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	2.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =5A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	5.8	A

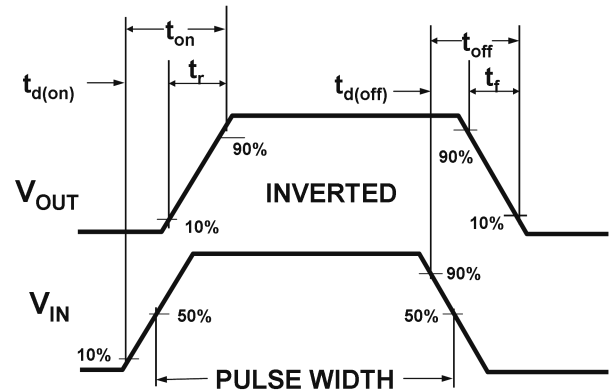
## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

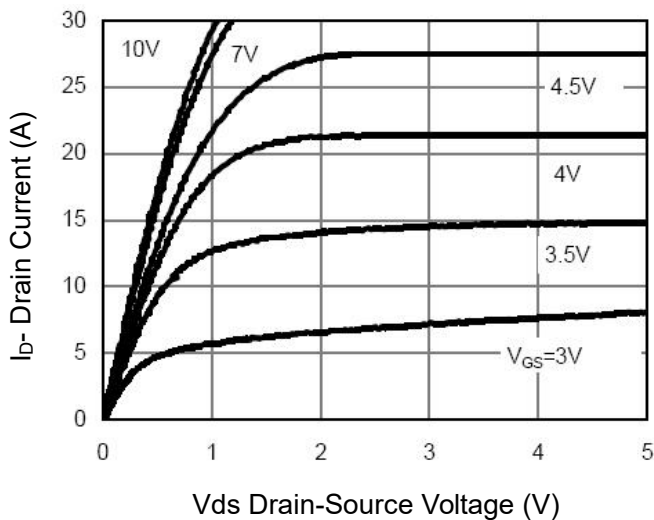
## Typical Electrical and Thermal Characteristics



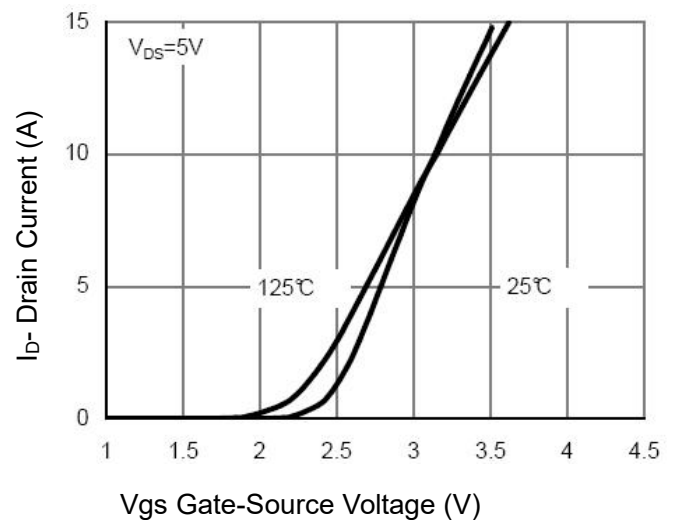
**Figure 1: Switching Test Circuit**



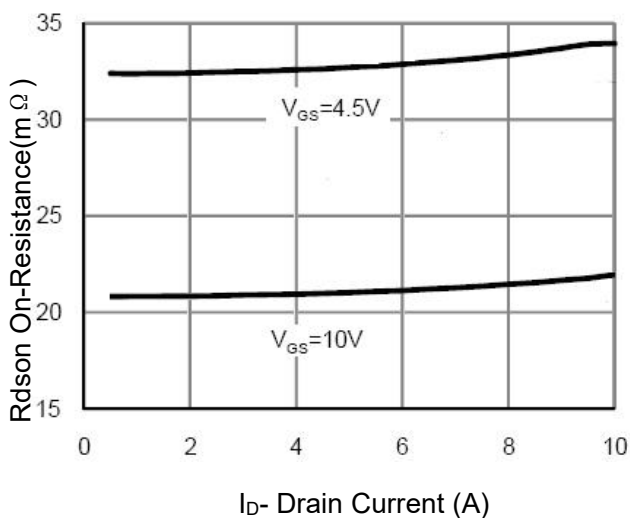
**Figure 2: Switching Waveforms**



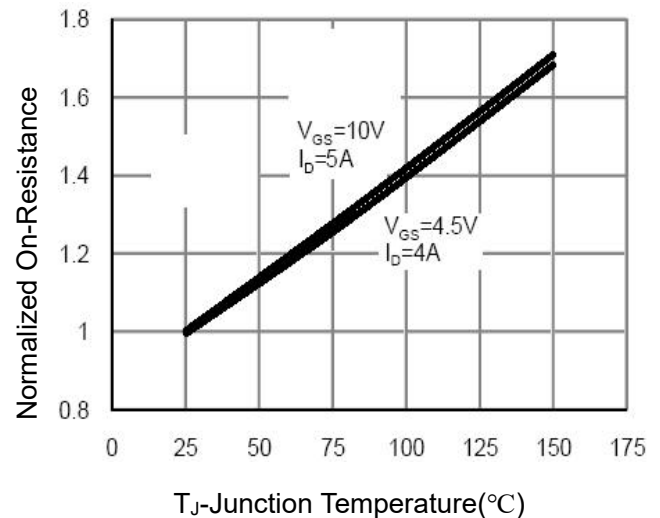
**Figure 3: Output Characteristics**



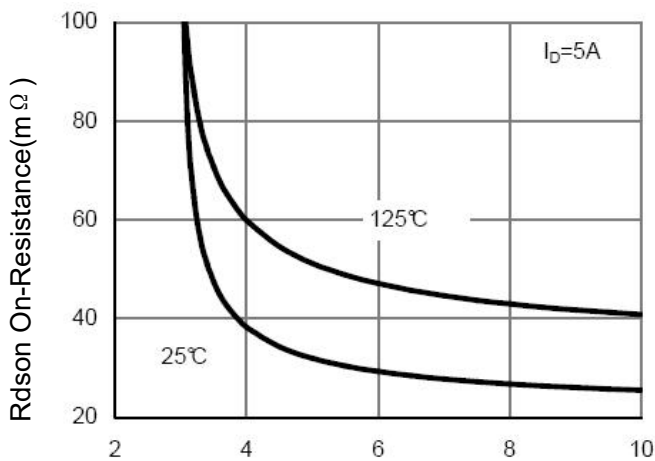
**Figure 4: Transfer Characteristics**



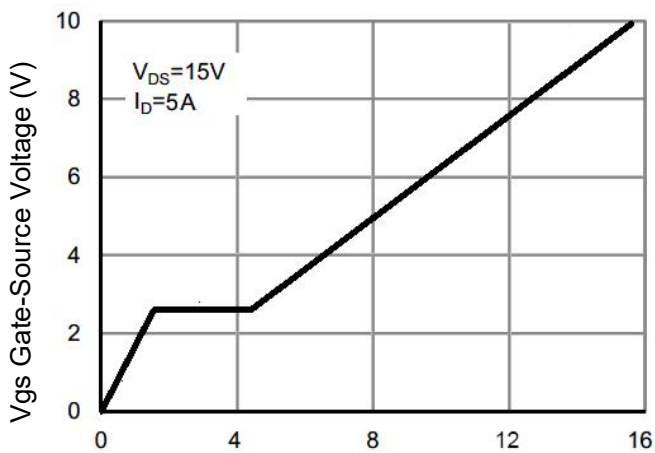
**Figure 5: Drain-Source On-Resistance**



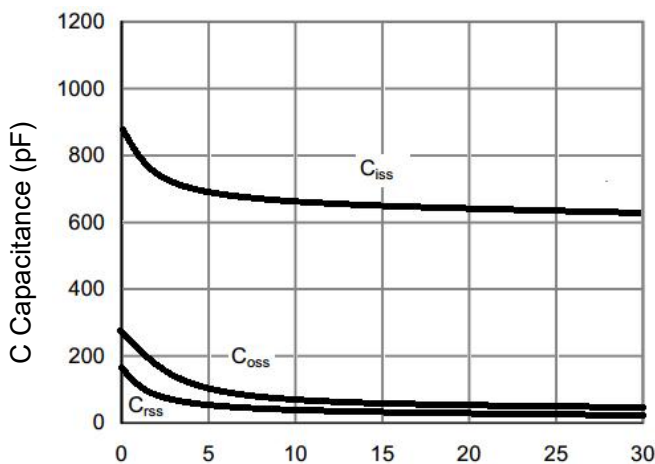
**Figure 6: Drain-Source On-Resistance**



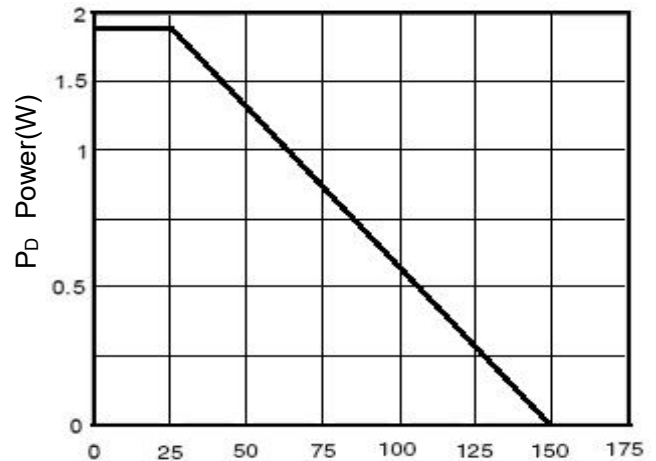
Vgs Gate-Source Voltage (V)  
**Figure 7 Rdson vs Vgs**



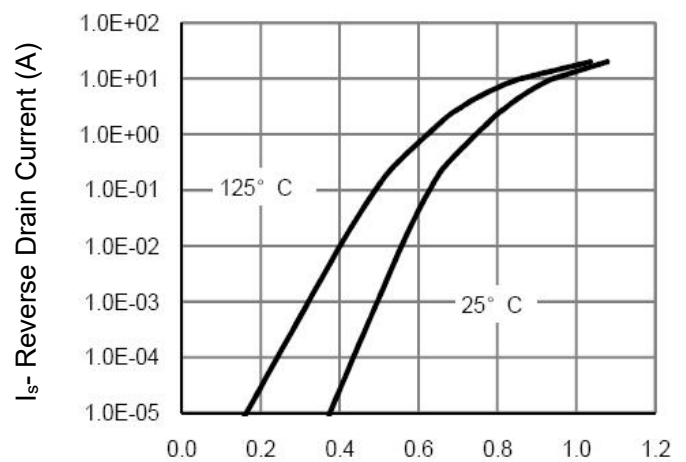
Qg Gate Charge (nC)  
**Figure 9 Gate Charge**



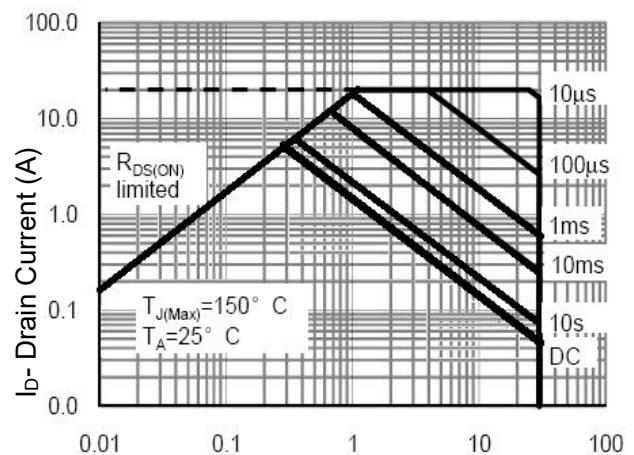
Vds Drain-Source Voltage (V)  
**Figure 11 Capacitance vs Vds**



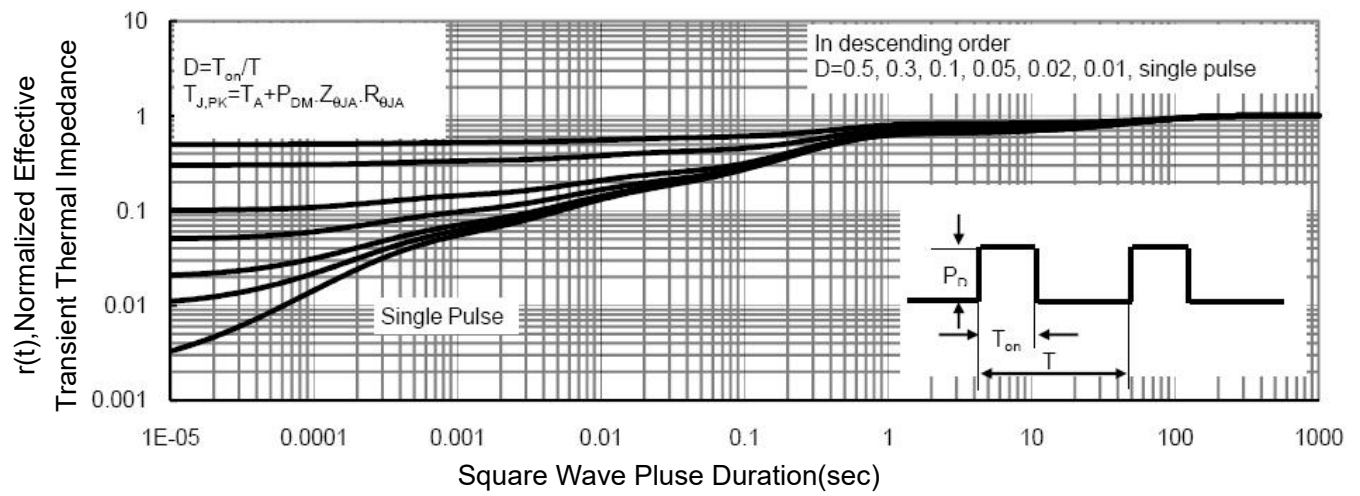
TJ-Junction Temperature(°C)  
**Figure 8 Power Dissipation**



Vds Drain-Source Voltage (V)  
**Figure 10 Source- Drain Diode Forward**

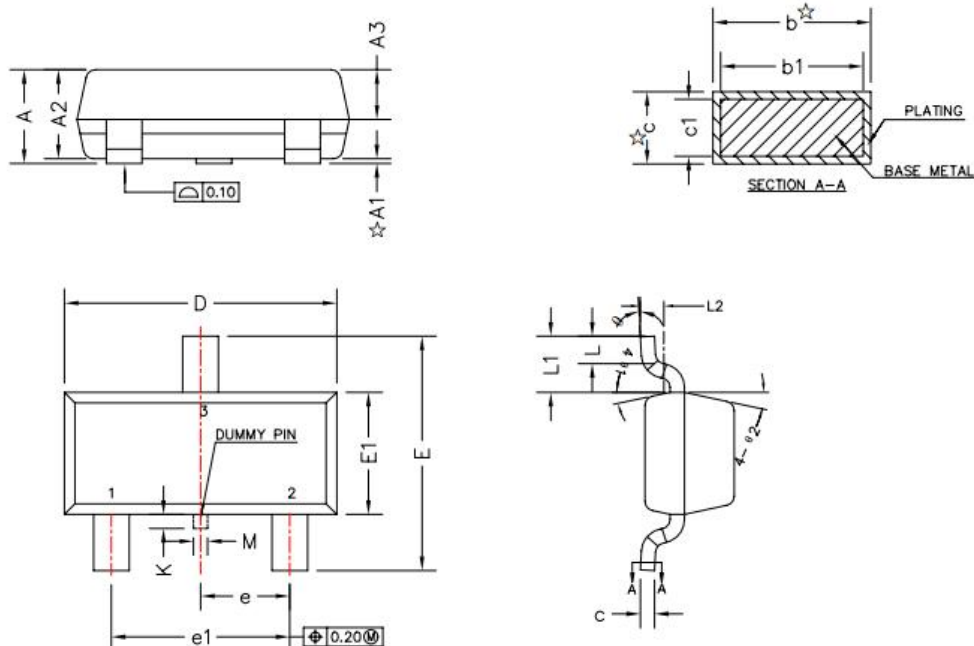


Vds Drain-Source Voltage (V)  
**Figure 12 Safe Operation Area**



**Figure 13 Normalized Maximum Transient Thermal Impedance**

## SOT-23 Package Information



Symbol	Millimeters	
	Min.	Max.
A	0.89	1.12
A1	0.01	0.10
A2	0.88	1.02
A3	0.43	0.63
b	0.36	0.50
b1	0.35	0.45
c	0.14	0.20
c1	0.14	0.16
D	2.80	3.00
E	2.35	2.64
E1	1.20	1.40
e	0.90	1.00
e1	1.80	2.00
L	0.40	0.60
L1	0.6REF	
L2	0.25BSC	
M	0.10	0.25
K	0.00	0.25
θ	0°	8°
θ1	10°	14°
θ2	10°	14°

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